

WHAT IS CLAIMED IS:

1 1. A semiconductor device comprising:

2 an encapsulater including an insulating resin, a tub,
3 first leads and tub-suspension leads exposed to a mounting
4 surface of said encapsulater, and a gate cured resin and
5 air vent cured resins which remain as a result of formation
6 of said encapsulater and which protrude from said
7 encapsulater; and

8 a semiconductor chip sealed in said encapsulater and
9 bonded on said tub, a plurality of said first leads being
10 electrically connected to said semiconductor chip and said
11 tub-suspension leads being joined to said tub;

12 wherein each of said gate cured resin and said air
13 vent cured resins exists in a portion between a respective
14 tub-suspension lead and a respective first lead with a
15 thickness identical to or smaller than a thickness of each
16 of resin burrs.

1 2. A semiconductor device comprising:

2 an encapsulater including an insulating resin, a tub,
3 first leads and tub-suspension leads exposed to a mounting
4 surface of said encapsulater, and a gate cured resin and
5 air vent cured resins which remain as a result of formation

6 of said encapsulater and which protrude from said
7 encapsulater; and
8 a semiconductor chip sealed in said encapsulater and
9 bonded on said tub, a plurality of said first leads being
10 electrically connected to said semiconductor chip and said
11 tub-suspension leads being joined to said tub;
12 wherein said gate cured resin and said air vent cured
13 resins respectively extend from edges of said encapsulater
14 with a predetermined thickness and have obverse and reverse
15 sides formed as flat surfaces.

1 3. The semiconductor device according to claim 2,
2 wherein said gate cured resin partly overlaps with the
3 respective tub-suspension lead.

1 4. The semiconductor device according to claim 2,
2 wherein said air vent cured resins partly overlap with
3 respective tub-suspension leads.

1 5. The semiconductor device according to claim 2,
2 wherein said gate cured resin partly overlaps with at least
3 one first lead.

1 6. The semiconductor device according to claim 2,
2 wherein each of said air vent cured resins partly overlaps
3 with at least one first lead.